

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
Form PTO-1449 (Modified)
(Use several sheets if necessary)

02/18/04

COMPLETE IF KNOWN

Application Number	10/782,564
Confirmation Number	
Filing Date	02/18/04
First Named Inventor	Jack Zezhong Peng
Group Art Unit	2827
Examiner Name	Huan Hoang
Attorney Docket No.	384848013US1

Sheet

1

of

4

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		NUMBER	Kind Code (if known)			
HJ		3,634,929		Yoshida et al.	01/18/72	
		4,322,822		McPherson	03/30/82	
		4,488,262		Basire et al.	12/11/84	
		4,490,900		Chiu	01/01/85	
		4,502,208		McPherson	03/05/85	
		4,507,757		McElroy	03/26/85	
		4,543,594		Mohsen et al.	09/24/85	
		4,546,273		Osman	10/08/85	
		4,599,705		Holmberg, et al.	07/08/86	
		4,613,886		Chwang	09/23/86	
		4,677,742		Johnson	07/07/87	
		4,758,986		Kuo	07/19/88	
		4,794,562		Kato et al.	12/27/88	
		4,823,181		Mohsen et al.	04/18/89	
		4,876,220		Mohsen et al.	10/24/89	
		4,899,205		Hamdy et al.	02/08/90	
		4,943,538		Mohsen et al.	07/24/90	
		4,962,342		Mead et al.	10/09/90	
		5,138,410		Takebuchi	08/11/92	
		5,150,179		Gill	09/22/92	
		5,303,185		Hazani	04/12/94	
		5,304,871		Dharmarajan et al.	04/19/94	
		5,323,342		Wada et al.	06/21/94	
		5,412,244		Hamdy et al.	05/02/95	
		5,477,499		Van Buskirk et al.	12/19/95	
		5,496,756		Sharma et al.	03/05/96	
		5,576,568		Kowshik	11/19/96	
HJ		5,578,848		Kwong et al.	11/26/96	

EXAMINER

Huan Hoang

DATE CONSIDERED

4/28/05

*EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application(s).

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT
Form PTO-1449 (Modified)
(Use several sheets if necessary)

02/18/04

COMPLETE IF KNOWN

Application Number	10/782,584
Confirmation Number	
Filing Date	02/18/04
First Named Inventor	Jack Zesheng Peng
Group Art Unit	2827
Examiner Name	Ivan Hwang

Sheet 2 of 4

Attorney Docket No. 384848013US1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		NUMBER	Kind Code (if known)			
HH		5,586,270		Rotier et al.	12/17/96	
		5,587,603		Kowshik	12/24/96	
		5,600,265		El Gamal et al.	02/04/97	
		5,675,541		Leterrier	10/07/97	
		5,675,547		Koga	10/07/97	
		5,745,417		Kobayashi et al.	04/28/98	
		5,825,200		Kolze	10/20/98	
		5,825,201		Kolze	10/20/98	
		5,880,512		Gordon et al.	03/09/99	
		5,909,049		McCollum	06/01/99	
		5,986,931		Caywood	11/16/99	
		5,986,939		Yamada	11/16/99	
		6,016,268		Worley	01/18/00	
		6,034,893		Mehta	03/07/00	
		6,040,968		Duvvury et al.	03/21/00	
		6,064,595		Logie et al.	05/16/00	
		6,084,428		Kolze et al.	07/04/00	
		6,097,077		Gordon et al.	08/01/00	
		6,157,568		Schmidt	12/05/00	
		6,168,954		Chem	12/26/00	
		6,214,666		Mehta	04/10/01	
		6,215,140		Reisinger et al.	04/10/01	
		6,218,274		Komatsu	04/17/01	
		6,232,631		Schmidt et al.	05/15/01	
		6,249,809		Bro	06/19/01	
		6,282,123		Mehta	08/28/01	
		6,294,809		Logie	09/25/01	
HH		6,297,103		Ahn et al.	10/02/01	

EXAMINER

Ivan Hwang

DATE CONSIDERED

4/28/05

*EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application(s).

INFORMATION DISCLOSURE STATEMENT BY APPLICANT Form PTO-1449 (Modified) (Use several sheets if necessary)				COMPLETE IF KNOWN	
				Application Number	10/782,564
				Confirmation Number	
				Filing Date	2/18/04
				First Named Inventor	Jack Zezhong Peng
				Group Art Unit	2827
Examiner Name	Huan Hoang				
Sheet	3	of	4	Attorney Docket No.	384848013US1

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.	U.S. Patent or Application		Name of Patentee or Inventor of Cited Document	Date of Publication or Filing Date of Cited Document
		NUMBER	Kind Code (if known)		
HU		6,304,666		Warren et al.	10/16/01
		6,351,428		Forbes	02/26/02
		6,421,293		Candelier et al.	07/16/02
		6,431,456		Nishizawa et al.	08/13/02
		6,456,535		Forbes et al.	09/24/02
HU		6,556,481		Hsu et al.	04/29/03
HU		US2001/0003374		Bohmer et al.	06/14/01

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No.	Foreign Patent or Application		Name of Patentee or Applicant of Cited Document	Date of Publication or Filing Date of Cited Document
		Office	NUMBER	Kind Code (if known)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
HU		EP	0 295 935	A1	Advanced Micro Devices, Inc. 12/21/88
HU		JP	61292295		Fujitsu Ltd. 12/23/86

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume/issue number(s), publisher, city and/or country where published.			
HU		MIRANDA, ENRIQUE et al; Analytic Modeling of Leakage Current Through Multiple Breakdown Paths in SiO ₂ Films; 39 th Annual International Reliability Physics Symposium; Orlando, FL 2001.			
		LOMBARDO, S. et al; Softening of Breakdown in Ultra-Thin Gate Oxide nMOSFET's at Low Inversion Layer Density; 39 th Annual International Reliability Physics Symposium; Orlando, FL 2001.			
		WU, E.W. et al; Voltage-Dependent Voltage-Acceleration of Oxide Breakdown for Ultra-Thin Oxides; IEEE, 2000.			
		RASRAS, MAHMOUD et al; Substrate Hole Current Origin After Oxide Breakdown; IEEE, 2000.			
HU		SUNE, JORDI et al; Post Soft Breakdown Conduction in SiO ₂ Gate Oxides; IEEE, 2000.			

EXAMINER	Huan Hoang	DATE CONSIDERED	4/28/05
*EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application(s).			

INFORMATION DISCLOSURE STATEMENT BY APPLICANT Form PTO-1449 (Modified) <i>02/18/04</i> (Use several sheets if necessary)				COMPLETE IF KNOWN	
Sheet	4	of	4	Application Number	10/782,564
				Confirmation Number	
				Filing Date	02/18/04
				First Named Inventor	Jack Zezhong Peng
				Group Art Unit	2827
				Examiner Name	<i>Haan Hoang</i>
				Attorney Docket No.	384848013US1

OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume/issue number(s), publisher, city and/or country where published.				T
<i>HH</i>		DeGRAAF, C., et al, A Novel High-Density Low-Cost Diode Programmable Read Only Memory, IEEE, 1996.				

EXAMINER	<i>Haan Hoang</i>	DATE CONSIDERED	<i>4/28/05</i>
*EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application(s).			